

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-THYRISTOR

TLP747JF

OFFICE MACHINE
SWITCHING POWER SUPPLY

The TOSHIBA TLP747JF consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

All parameters are tested to the specification of TLP747J.
(both condition and limits)

- Peak Off-State Voltage : 600V (Min.)
- Trigger LED Current : 15mA (Max.)
- On-State Current : 150mA (Max.)
- UL Recognized : UL1577, File No.E67349
- BSI Approved : BS EN60065 : 1994,
Certificate No. 7364
BS EN60950 : 1992,
Certificate No. 7365
- SEMKO Approved : SS4330784, Certificate No. 9325163
No. 9522142
- Isolation Voltage : 4000Vrms (Min.)
- Option (D4) type
VDE Approved : DIN VDE0884 / 06.92,
Certificate No. 74286, 91808

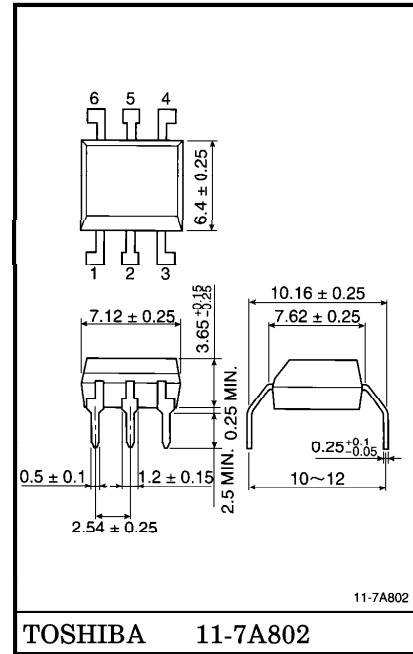
Maximum Operating Insulation Voltage : 890, 1130V_{PK}

Highest Permissible Over Voltage : 6000, 8000V_{PK}

(Note) When a VDE0884 approved type is needed,
please designate the "Option (D4)"

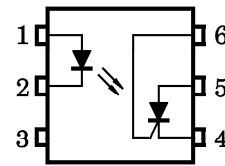
- Creepage Distance : 8.0mm (Min.)
- Clearance : 8.0mm (Min.)
- Internal Creepage Path : 4.0mm (Min.)
- Insulation Thickness : 0.5mm (Min.)
- Conforming Safety Standards :
DIN 57 804.VDE0804 / 1.83
DIN IEC65 / VDE0860 / 8.81
DIN IEC380 / VDE0806 / 8.81
DIN IEC435 / VDE0805 / Draft Nov.84
DIN IEC601T1 / VDE0750T1 / 5.82
BS7002 : 1989 (EN60950)

Unit in mm



Weight : 0.42g

PIN CONFIGURATIONS (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : NC
- 4 : CATHODE
- 5 : ANODE
- 6 : GATE

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